Product data sheet

## 1. Product profile

#### 1.1 General description

Planar PIN diode in a SOD523 ultra small SMD plastic package.

#### 1.2 Features and benefits

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance

### 1.3 Applications

- RF attenuators and switches
- Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch

## 2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------|--------------------|----------------|
| 1   | cathode     |                    | 1.4            |
| 2   | anode       | 1 2                | sym006         |

# 3. Ordering information

Table 2. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| BAP65-02    | -       | plastic surface-mounted package; 2 leads | SOD523  |

## 4. Marking

Table 3. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BAP65-02    | K6           |



Silicon PIN diode

# 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                  | Conditions             | Min | Max  | Unit |
|------------------|----------------------------|------------------------|-----|------|------|
| $V_R$            | continuous reverse voltage |                        | -   | 30   | V    |
| I <sub>F</sub>   | continuous forward current |                        | -   | 100  | mA   |
| P <sub>tot</sub> | total power dissipation    | T <sub>s</sub> ≤ 90 °C | -   | 715  | mW   |
| T <sub>stg</sub> | storage temperature        |                        | -65 | +150 | °C   |
| Tj               | junction temperature       |                        | -65 | +150 | °C   |
| T <sub>amb</sub> | ambient temperature        |                        | -40 | +85  | °C   |

### 6. Thermal characteristics

Table 5. Thermal characteristics

| Symbol              | Parameter   | Conditions | Тур | Unit |
|---------------------|---|------------|-----|------|
| R <sub>th j-s</sub> | thermal resistance from junction to soldering point |            | 85  | K/W  |

### 7. Characteristics

Table 6. Characteristics

 $T_i = 25$  °C unless otherwise specified.

| Symbol                 | Parameter                | Conditions                                     | Min          | Тур   | Max  | Unit |
|------------------------|--------------------------|--|--------------|-------|------|------|
| $V_{F}$                | forward voltage          | $I_F = 50 \text{ mA}$                          | -            | 0.9   | 1.1  | V    |
| I <sub>R</sub>         | reverse leakage current  | V <sub>R</sub> = 20 V                          | -            | -     | 20   | nA   |
| C <sub>d</sub>         | diode capacitance        | $V_R = 0 V$ ; $f = 1 MHz$                      | -            | 0.65  | -    | pF   |
|                        |                          | $V_R = 1 V; f = 1 MHz$                         | -            | 0.55  | 0.9  | pF   |
|                        |                          | $V_R = 3 V; f = 1 MHz$                         | -            | 0.5   | 0.8  | pF   |
|                        |                          | $V_R = 20 \text{ V}; f = 1 \text{ MHz}$        | -            | 0.375 | -    | pF   |
| $r_D$                  | diode forward resistance | $I_F = 1 \text{ mA}; f = 100 \text{ MHz}$      | -            | 1     | -    | Ω    |
|                        |                          | $I_F = 5 \text{ mA}; f = 100 \text{ MHz}$      | [1] -        | 0.65  | 0.95 | Ω    |
|                        |                          | $I_F = 10 \text{ mA}; f = 100 \text{ MHz}$     | <u>[1]</u> - | 0.56  | 0.9  | Ω    |
|                        |                          | $I_F = 100 \text{ mA}$ ; $f = 100 \text{ MHz}$ | -            | 0.35  | -    | Ω    |
| $ s_{21} ^2$ isolation | isolation                | $V_R = 0$ ; $f = 900 \text{ MHz}$              | -            | 10    | -    | dB   |
|                        |                          | $V_R = 0$ ; $f = 1800 \text{ MHz}$             | -            | 5.8   | -    | dB   |
|                        |                          | $V_R = 0$ ; $f = 2450 \text{ MHz}$             | -            | 4.4   | -    | dB   |
| $ s_{21} ^2$           | insertion loss           | $I_F = 1 \text{ mA}; f = 900 \text{ MHz}$      | -            | 0.11  | -    | dB   |
|                        |                          | $I_F = 1 \text{ mA}; f = 1800 \text{ MHz}$     | -            | 0.13  | -    | dB   |
|                        |                          | $I_F = 1 \text{ mA}$ ; $f = 2450 \text{ MHz}$  | -            | 0.16  | -    | dB   |
| $ s_{21} ^2$           | insertion loss           | $I_F = 5 \text{ mA}; f = 900 \text{ MHz}$      | -            | 0.08  | -    | dB   |
|                        |                          | $I_F = 5 \text{ mA}; f = 1800 \text{ MHz}$     | -            | 0.11  | -    | dB   |
|                        |                          | $I_F = 5 \text{ mA}; f = 2450 \text{ MHz}$     | -            | 0.13  | -    | dB   |

BAP65-02

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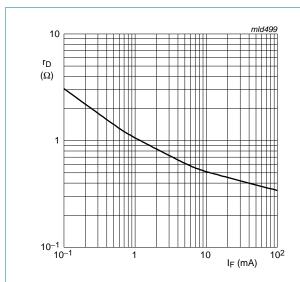
Silicon PIN diode

**Table 6.** Characteristics ...continued  $T_i = 25$  °C unless otherwise specified.

| Symbol          | Parameter                                | Conditions  | Min   | Тур  | Max | Unit |
|-----------------|--|---|-------|------|-----|------|
| $ s_{21} ^2$ ir | insertion loss                           | $I_F = 10 \text{ mA}; f = 900 \text{ MHz}$  | -     | 0.07 | -   | dB   |
|                 |  | $I_F = 10 \text{ mA}; f = 1800 \text{ MHz}$   | -     | 0.1  | -   | dB   |
|                 |  | $I_F = 10 \text{ mA}$ ; $f = 2450 \text{ MHz}$  | -     | 0.13 | -   | dB   |
| $ s_{21} ^2$    | insertion loss                           | $I_F = 100 \text{ mA}; f = 900 \text{ MHz}$   | -     | 0.07 | -   | dB   |
|                 | I <sub>F</sub> = 100 mA;<br>f = 1800 MHz | -   | 0.1   | -    | dB  |      |
|                 | I <sub>F</sub> = 100 mA;<br>f = 2450 MHz | -   | 0.128 | -    | dB  |      |
| τ∟              | charge carrier life time                 | when switched from $I_F = 10$ mA to $I_R = 6$ mA; $R_L = 100$ $\Omega$ ; measured at $I_R = 3$ mA | -     | 0.17 | -   | μS   |
| L <sub>S</sub>  | series inductance                        | $I_F = 100 \text{ mA}$ ; $f = 100 \text{ MHz}$  | -     | 0.6  | -   | nΗ   |

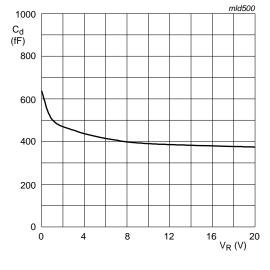
<sup>[1]</sup> Guaranteed on AQL basis: inspection level S4, AQL 1.0.

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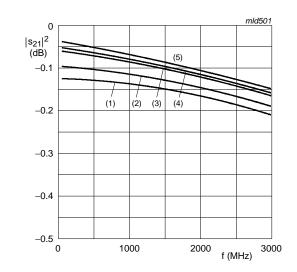
 $f = 100 \text{ MHz}; T_j = 25 \text{ }^{\circ}\text{C}$ 

Fig 1. Forward resistance as a function of forward current; typical values



 $f = 1 \text{ MHz}; T_j = 25 ^{\circ}\text{C}$ 

Fig 2. Diode capacitance as a function of reverse voltage; typical values



(1)  $I_F = 0.5 \text{ mA}$ 

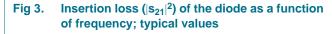
(2)  $I_F = 1 \text{ mA}$ 

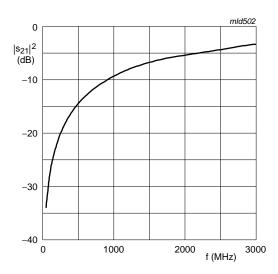
(3)  $I_F = 5 \text{ mA}$ 

(4)  $I_F = 10 \text{ mA}$ 

(5)  $I_F = 100 \text{ mA}$ 

Diode inserted in series with a 50  $\Omega$  stripline circuit and biased via the analyzer Tee network. T<sub>amb</sub> = 25 °C.





Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit.  $T_{amb}$  = 25  $^{\circ}C.$ 

Fig 4. Isolation ( $|s_{21}|^2$ ) of the diode as a function of frequency; typical values

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# 8. Package outline

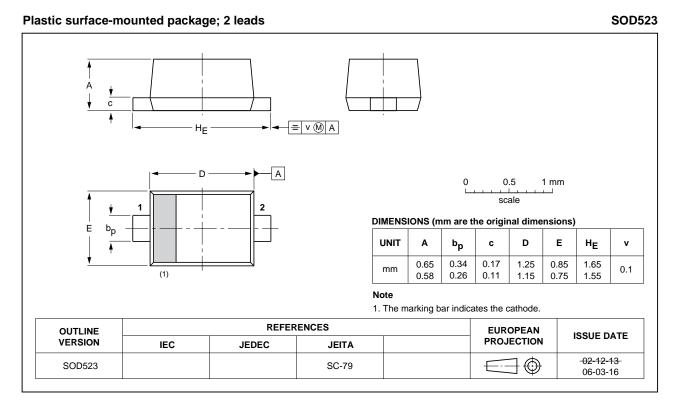


Fig 5. Package outline SOD523

Silicon PIN diode

# 9. Revision history

#### Table 7. Revision history

| Document ID                      | Release date                      | Data sheet status                                     | Change notice       | Supersedes           |
|----------------------------------|-----------------------------------|---|---------------------|----------------------|
| BAP65-02 v.5                     | 20100928                          | Product data sheet                                    | -                   | BAP65-02_N v.4       |
| Modifications:                   |                                   | f this data sheet has been red<br>NXP Semiconductors. | esigned to comply w | ith the new identity |
|                                  | <ul> <li>Legal texts h</li> </ul> | ave been updated.                                     |                     |                      |
|                                  | <ul> <li>Table 4 "Limi</li> </ul> | ting values": added T <sub>amb</sub> (amb             | ient temperature).  |                      |
| BAP65-02_N v.4                   | 20080108                          | Product data sheet                                    | -                   | BAP65-02 v.3         |
| BAP65-02 v.3<br>(9397 750 08364) | 20010511                          | Product specification                                 | -                   | BAP65-02 v.2         |
| BAP65-02 v.2<br>(9397 750 08237) | 20010507                          | Product specification                                 | -                   | BAP65-02 v.1         |
| BAP65-02 v.1<br>(9397 750 07724) | 20001220                          | Product specification                                 | -                   | -                    |

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|--------------------------------|-------------------|---|
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| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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#### Silicon PIN diode

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